

isc P-Channel MOSFET Transistor

2N6898

DESCRIPTION

- SOA is power-dissipation limited
- Nanosecond switching speeds
- Linear transfer characteristics
- High input impedance
- Majority carrier device

APPLICATIONS

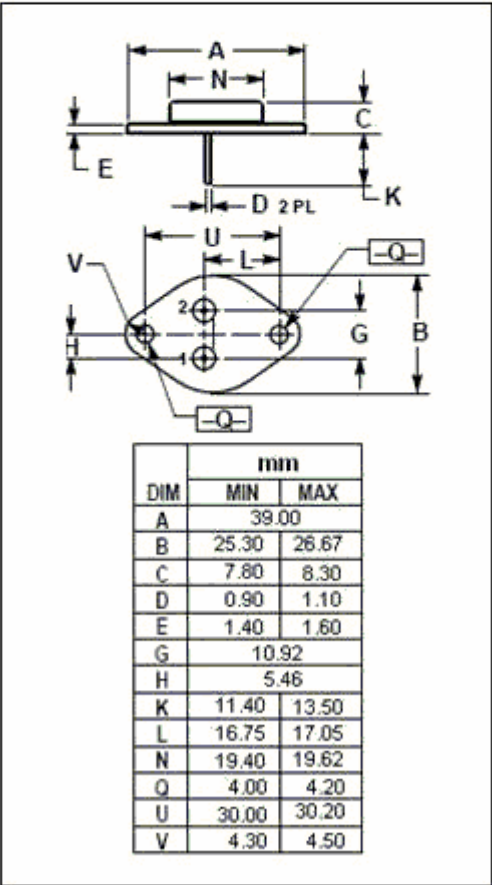
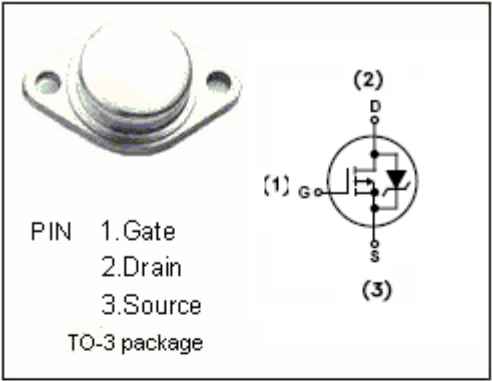
- The 2N6898 is designed for application such as switching regulators,switching converters,motor drivers, relay drivers and drivers for high-power bipolar switching transistors requiring high speed and low gate-driver power

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	ARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage (V _{GS} =0)	-100	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current-continuous@ TC=37°C	-25	A
P _{tot}	Total Dissipation@TC=25°C	150	W
T _j	Max. Operating Junction Temperature	-55~150	°C
T _{stg}	Storage Temperature Range	-55~150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance,Junction to Case	0.83	°C/W



isc P-Channel Mosfet Transistor**2N6898****• ELECTRICAL CHARACTERISTICS (T_C=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = -1mA	-100		V
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D = -0.25mA	-2	-4	V
R _{DS(ON)}	Drain-Source On-stage Resistance	V _{GS} = -10V; I _D = -15.8A		0.2	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = -20V; V _{DS} = 0		-100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -80V, V _{GS} = 0		-1	uA
V _{SD}	Diode Forward Voltage	I _F = -25A; V _{GS} = 0		1.6	V